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Kind regards,

Team Nexperia

NPN resistor-equipped transistors; $R1 = 100 \text{ k}\Omega$, R2 = openRev. 04 — 17 February 2005Product data sheet

1. **Product profile**

1.1 General description

NPN resistor-equipped transistors.

Table 1: **Product overview**

Type number	Package		PNP complement
	Philips	JEITA	
PDTC115TE	SOT416	SC-75	PDTA115TE
PDTC115TK	SOT346	SC-59A	PDTA115TK
PDTC115TM	SOT883	SC-101	PDTA115TM
PDTC115TS ^[1]	SOT54 (TO-92)	SC-43A	PDTA115TS
PDTC115TT	SOT23	-	PDTA115TT
PDTC115TU	SOT323	SC-70	PDTA115TU

Reduces component count

Circuit drivers

Reduces pick and place costs

[1] Also available in SOT54A and SOT54 variant packages (see Section 2).

1.2 Features

- Built-in bias resistor
- Simplifies circuit design

1.3 Applications

- General-purpose switching and amplification
- Inverter and interface circuits

1.4 Quick reference data

Table 2: **Quick reference data**

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
I _O	output current (DC)		-	-	100	mA
R1	bias resistor 1 (input)		70	100	130	kΩ



NPN resistor-equipped transistors; R1 = 100 kΩ, R2 = open

2. Pinning information

Pin	Description	Simplified outline	Symbol
SOT54			
1	input (base)		
2	output (collector)		
3	GND (emitter)	001aab347	1 3 006aaa218
SOT54A			
1	input (base)		
2	output (collector)		2
3	GND (emitter)	1 2 3 001aab348	1 3 006aaa218
SOT54 va	ariant		
1	input (base)		
2	output (collector)		
3	GND (emitter)	(1) (2) (2) (3) (0)1aab447	1 R1 3 006aaa218
SOT23, S	OT323, SOT346, SOT416		
1	input (base)		
2	GND (emitter)	3	3
3	output (collector)	1 2 006aaa144	1 2 sym012
SOT883			
1	input (base)		
2	GND (emitter)		3
3	output (collector)	2 Transparent top view	1 2 sym012

9397 750 14021 Product data sheet

NPN resistor-equipped transistors; R1 = 100 kΩ, R2 = open

3. Ordering information

Table 4: Ordering information							
Type number	Package						
	Name	Description	Version				
PDTC115TE	SC-75	plastic surface mounted package; 3 leads	SOT416				
PDTC115TK	SC-59A	plastic surface mounted package; 3 leads	SOT346				
PDTC115TM	SC-101	leadless ultra small plastic package; 3 solder lands; body $1.0\times0.6\times0.5~\text{mm}$	SOT883				
PDTC115TS ^[1]	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54				
PDTC115TT	-	plastic surface mounted package; 3 leads	SOT23				
PDTC115TU	SC-70	plastic surface mounted package; 3 leads	SOT323				

[1] Also available in SOT54A and SOT54 variant packages (see <u>Section 2</u> and <u>Section 9</u>).

4. Marking

Table 5: Marking codes	
Type number	Marking code [1]
PDTC115TE	17
PDTC115TK	28
PDTC115TM	G5
PDTC115TS	TC115T
PDTC115TT	*AK
PDTC115TU	*17

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = open

5. Limiting values

Table 6: In accorda	Limiting values nce with the Absolute Maximu	Im Rating System	(IEC 60134).		
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	50	V
V _{CEO}	collector-emitter voltage	open base	-	50	V
V _{EBO}	emitter-base voltage	open collector	-	5	V
lo	output current (DC)		-	100	mA
I _{CM}	peak collector current		-	100	mA
P _{tot}	total power dissipation				
	SOT416	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> -	150	mW
	SOT346	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	250	mW
	SOT883	$T_{amb} \le 25 \ ^{\circ}C$	[2] [3]	250	mW
	SOT54	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	500	mW
	SOT23	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	250	mW
	SOT323	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C

[1] Refer to standard mounting conditions.

[2] Reflow soldering is the only recommended soldering method.

[3] Refer to SOT883 standard mounting conditions; FR4 printed-circuit board with 60 µm copper strip line.

6. Thermal characteristics

Table 7:	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	SOT416		<u>[1]</u> _	-	833	K/W
	SOT346		<u>[1]</u> _	-	500	K/W
	SOT883		[2] [3]	-	500	K/W
	SOT54		<u>[1]</u> _	-	250	K/W
	SOT23		<u>[1]</u> _	-	500	K/W
	SOT323		<u>[1]</u> _	-	625	K/W

[1] Refer to standard mounting conditions.

[2] Reflow soldering is the only recommended soldering method.

[3] Refer to SOT883 standard mounting conditions; FR4 printed-circuit board with 60 µm copper strip line.

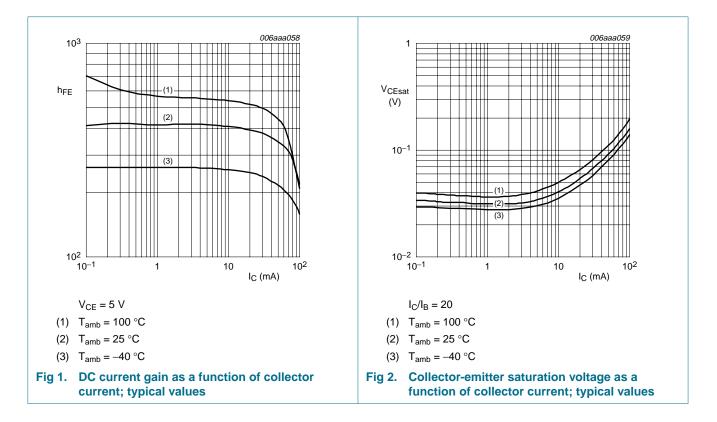
NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = open

7. Characteristics

Table 8: Characteristics

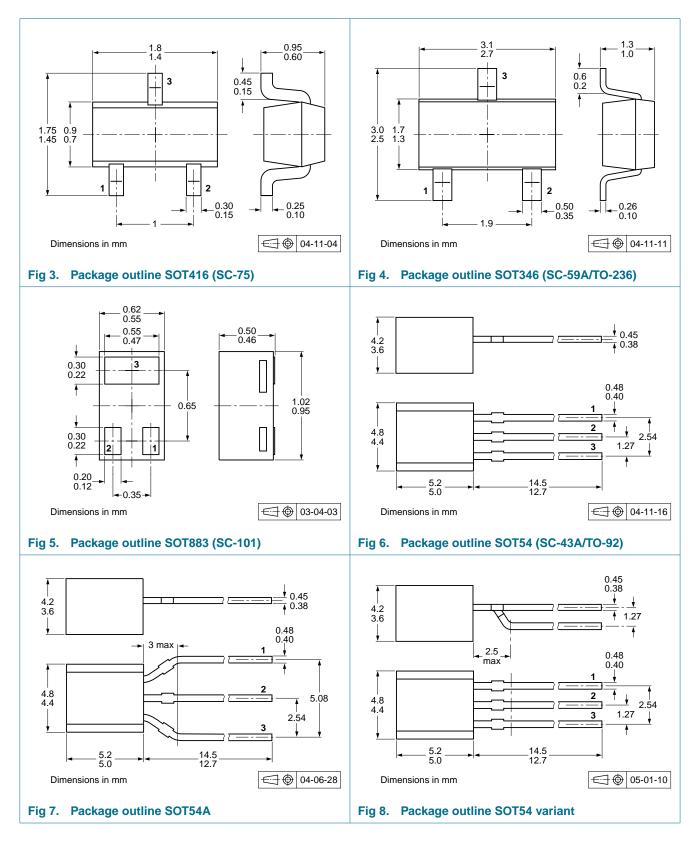
 $T_{amb} = 25 \circ C$ unless otherwise specified.

	-					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
-OLO	collector-emitter	$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0 \text{ A}$	-	-	1	μΑ
	cut-off current	$V_{CE} = 30 \text{ V}; I_B = 0 \text{ A};$ $T_j = 150 \text{ °C}$	-	-	50	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 V; I_C = 0 A$	-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 1 \text{ mA}$	100	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = 5 \text{ mA}; I_{B} = 0.25 \text{ mA}$	-	-	150	mV
R1	bias resistor 1 (input)		70	100	130	kΩ
C _c	collector capacitance	$I_E = i_e = 0 \text{ A}; V_{CB} = 10 \text{ V};$ f = 1 MHz	-	-	2.5	pF



NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = open

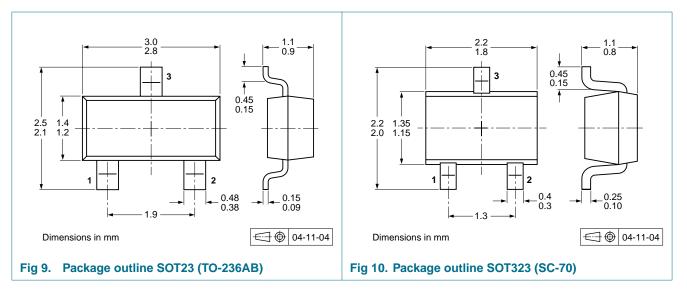
8. Package outline



Philips Semiconductors

PDTC115T series

NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = open



9. Packing information

Table 9:Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing o	Packing quantity		
			3000	5000	10000	
PDTC115TE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135	
PDTC115TK	SOT346	4 mm pitch, 8 mm tape and reel	-115	-	-135	
PDTC115TM	SOT883	2 mm pitch, 8 mm tape and reel	-	-	-315	
PDTC115TS	SOT54	bulk, straight leads	-	-412	-	
PDTC115TS	SOT54A	tape and reel, wide pitch	-	-	-116	
PDTC115TS	SOT54A	tape ammopack, wide pitch	-	-	-126	
PDTC115TS	SOT54 variant	bulk, delta pinning	-	-112	-	
PDTC115TT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235	
PDTC115TU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135	

[1] For further information and the availability of packing methods, see Section 14.

NPN resistor-equipped transistors; R1 = 100 kΩ, R2 = open

10. Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
PDTC115T_SER_4	20050217	Product data sheet	-	9397 750 14021	PDTC115TT_3
Modifications	 The types added. 	PDTC115TE, PDTC11	5TK, PDTC115TM, F	DTC115TS and PD	C115TU were
	 Table 1 "P 	roduct overview" added	l		
	 Figure 1 a 	nd <mark>2</mark> added			
	 Section 9 ^c 	"Packing information" a	dded		
PDTC115TT_3	20040727	Product data sheet	-	9397 750 13505	PDTC115TT_2
PDTC115TT_2	20040510	Objective data sheet	-	9397 750 13206	PDTC115TT_1
PDTC115TT 1	20040305	Objective data sheet	-	9397 750 12554	-

NPN resistor-equipped transistors; R1 = 100 kΩ, R2 = open

11. Data sheet status

Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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PDTC115T series

NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = open

15. Contents

1	Product profile 1
1.1	General description
1.2	Features
1.3	Applications 1
1.4	Quick reference data 1
2	Pinning information 2
3	Ordering information 3
4	Marking 3
5	Limiting values 4
6	Thermal characteristics 4
7	Characteristics 5
8	Package outline 6
9	Packing information7
10	Revision history 8
11	Data sheet status
12	Definitions 9
13	Disclaimers 9
14	Contact information9



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Date of release: 17 February 2005 Document number: 9397 750 14021

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